

**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Inductive heating
- Electronic welders
- Self-commutated inverters

**Part No. Y70KFE-KT60cT**

$I_{T(AV)}$	2500A
$V_{DRM}$	800V~2000V
$V_{RRM}$	1000V~1800V
$t_q$	15~75μs

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT			
				Min	Type	Max				
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled	125			2500	A			
$V_{DRM}$	Repetitive peak off-state voltage	tp=10ms	125	800		2000	V			
$V_{RRM}$	Repetitive peak reverse voltage			1000		1800	V			
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			200	mA			
$I_{TSM}$	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			29	kA			
$I^2t$	$I^2t$ for fusing coordination					4205	$10^3 A^2s$			
$V_{TO}$	Threshold voltage					1.10	V			
$r_T$	On-state slope resistance		125			0.13	$m\Omega$			
$V_{TM}$	Peak on-state voltage			15≤ $t_q$ ≤28			2.20	V		
				29≤ $t_q$ ≤50			2.00	V		
				51≤ $t_q$ ≤75			1.80	V		
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	$V/\mu s$			
$di/dt$	Critical rate of rise of on-state current (Non-repetitive)	$V_{DM}=67\%V_{DRM}$ , Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1500	$A/\mu s$			
$Q_{rr}$	Recovery charge	$I_{TM}=2000A$ , tp=4000μs, $di/dt=-20A/\mu s$ , $V_R=100V$	125		750		$\mu C$			
$t_q$	Circuit commutated turn-off time	$I_{TM}=2000A$ , tp=4000μs, $V_R=100V$ $dv/dt=30V/\mu s$ , $di/dt=-20A/\mu s$	125	15		75	$\mu s$			
$I_{GT}$	Gate trigger current	$V_A=12V$ , $I_A=1A$	25	40		250	mA			
$V_{GT}$	Gate trigger voltage			0.9		2.5	V			
$I_H$	Holding current			20		1000	mA			
$I_L$	Latching current					1000	mA			
$V_{GD}$	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V			
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 32kN				0.012	$^{\circ}C/W$			
$R_{th(c-h)}$	Thermal resistance case to heatsink					0.003				
$F_m$	Mounting force			30		40	kN			
$T_{vj}$	Junction temperature			-40		125	$^{\circ}C$			
$T_{stg}$	Stored temperature			-40		130	$^{\circ}C$			
$W_t$	Weight				880		g			
Outline		KT60cT								

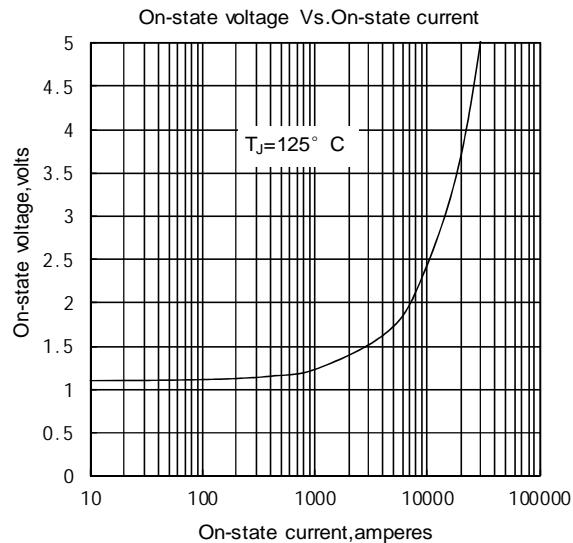


Fig.1

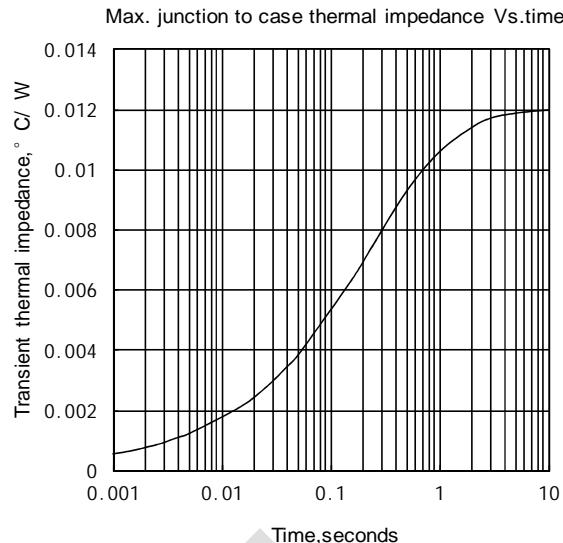


Fig.2

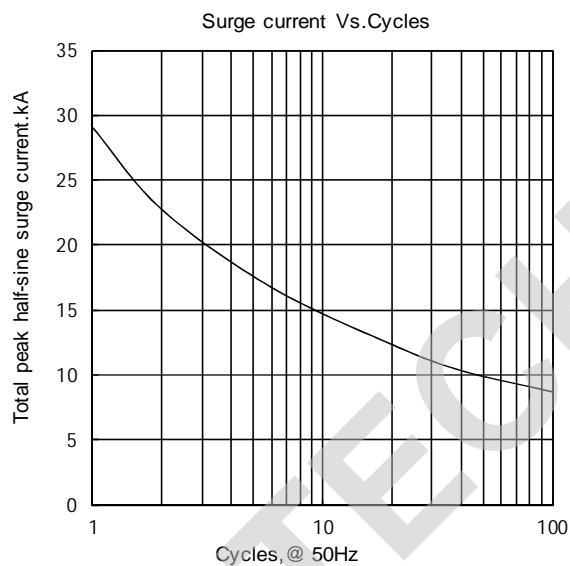


Fig.3

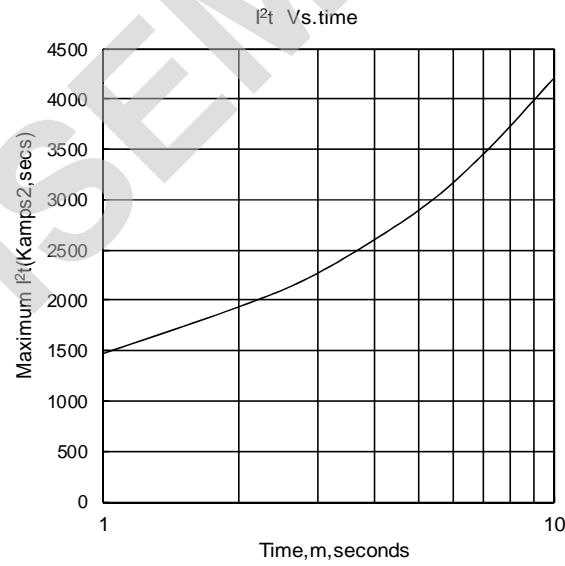


Fig.4

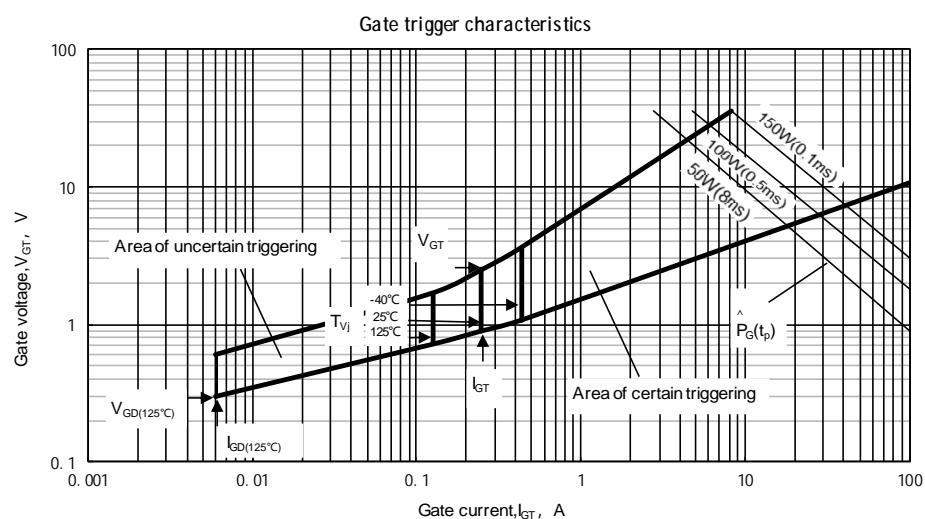
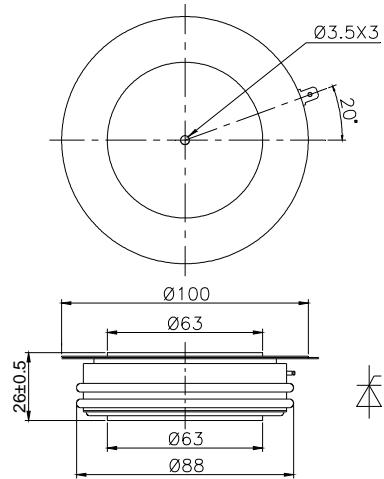


Fig.5

**Outline:**

TECHSEM reserves the right to change specifications without notice.